

# UMH14N / IMH14A

#### NPN 100mA 50V Complex Digital Transistors (Bias Resistor Built-in Transistors)

Parameter	Tr1 and Tr2
$V_{CEO}$	50V
I <sub>C</sub>	100mA
$R_1$	47kΩ

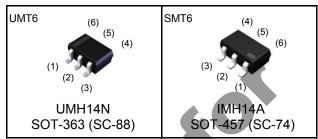
#### Features

- 1) Built-In Biasing Resistors.
- 2) Two DTC144T chips in one package.
- 3) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 4) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 5) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 6) Lead Free/RoHS Compliant.

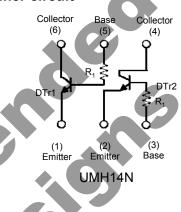
#### Application

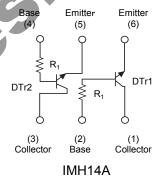
Inverter circuit, Interface circuit, Driver circuit

#### Outline



#### •Inner circuit





#### Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
UMH14N	UMT6	2021	TN	180	8	3,000	H14
IMH14A	SMT6	2928	T110	180	8	3,000	H14

## ● Absolute maximum ratings (Ta = 25°C)

#### <For DTr1 and DTr2 in common>

Parameter		Symbol	Values	Unit
Collector-base voltage		$V_{CBO}$	50	V
Collector-emitter voltage		$V_{CEO}$	50	V
Emitter-base voltage		V <sub>EBO</sub> 5		V
Collector current		I <sub>C</sub> *1	100	mA
Collector Power dissipation UMH14N IMH14A		P <sub>D</sub> *2	150 (Total)*3	mW
			300 (Total)*4	mW
Junction temperature		T <sub>j</sub>	150	°C
Range of storage temperature		T <sub>stg</sub>	-55 to +150	°C

## ●Electrical characteristics(Ta = 25°C)

## <For DTr1 and DTr2 in common>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	BV <sub>CBO</sub>	I <sub>C</sub> = 50μA	50	-	-	V
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	I <sub>C</sub> = 1mA	50	-	-	V
Emitter-base breakdown voltage	BV <sub>EBO</sub>	l <sub>E</sub> = 50μA	5	-	-	V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 50V	-	1	0.5	μА
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 4V	ı	1	0.5	μА
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C / I_B = 10 \text{mA} / 1 \text{mA}$	ı	1	0.3	V
DC current gain	h <sub>FE</sub>	$V_{CE}$ = 5V , $I_{C}$ = 1mA	100	250	600	-
Input resistance	R <sub>1</sub>	-	32.9	47	61.1	kΩ
Transition frequency	f <sub>T</sub> *1	$V_{CE} = 10V, I_{E} = -5mA$ f = 100MHz	-	250	-	MHz

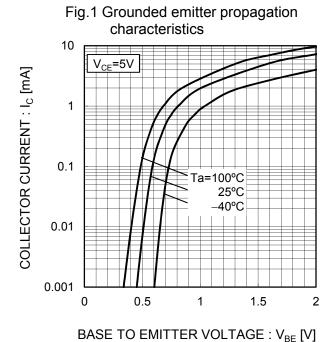
<sup>\*1</sup> Characteristics of built-in transistor

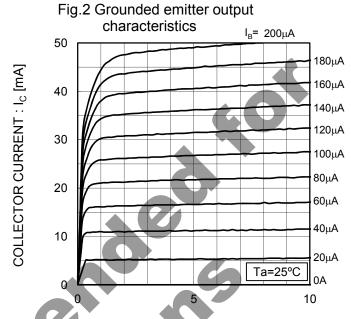
<sup>\*2</sup> Each terminal mounted on a reference footprint

<sup>\*3 120</sup>mW per element must not be exceeded.

<sup>\*4 200</sup>mW per element must not be exceeded.

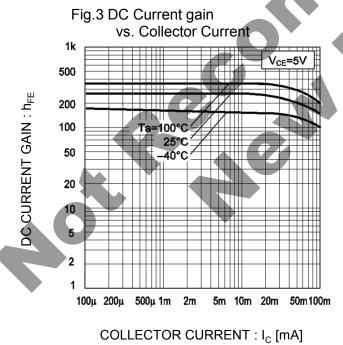
#### ●Electrical characteristic curves (Ta = 25°C) <For DTr1 and DTr2 in common>





COLLECTOR TO EMITTER VOLTAGE :  $V_{CE}\left[V\right]$ 

Fig.4 Collector-emitter saturation voltage



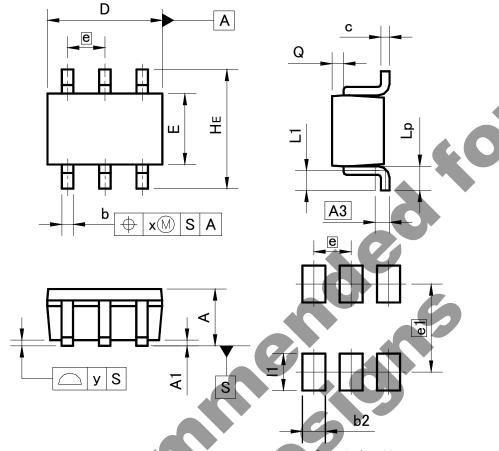
vs. Collector Current  $I_{C}/I_{B}=10$ 500m 200m VOLTAGE: V<sub>CE(sat)</sub> [V] Ta=100°C 100m 25°C 50m 40°C 20m 10m 5m 2m 1m  $100\mu$   $200\mu$ 2m 5m 10m 20m 50m100m 500μ 1m

COLLECTOR CURRENT : I<sub>C</sub> [mA]

COLLECTOR SATURATION

## ●Dimensions (Unit : mm)

UMT6



Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

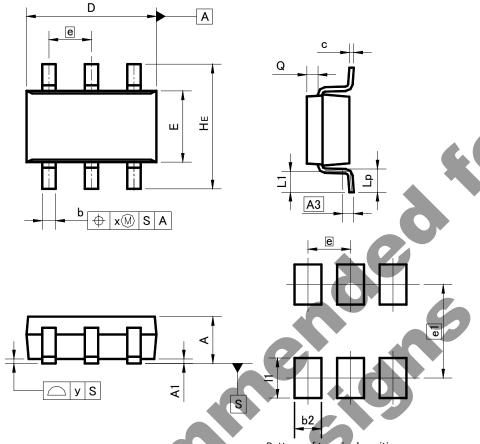
DIM	MILIMETERS		INC	HES
DIIVI	MIN	MAX	MIN	MAX
Α	0.80	1.00	0.031	0.039
A1	0.00	0.10	0.000	0.004
A3	0.	0.25 0.010		
b	0.15	0.30	0.006	0.012
C	0.10	0.20	0.004	0.008
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
е	0.65		0.026	
HE	2.00	2.20	0.079	0.087
L1	0.20	0.50	0.008	0.020
Lp	0.25	0.55	0.010	0.022
Q	0.10	0.30	0.004	0.012
Х		0.10	_	0.004
У		0.10	_	0.004

DIM MI		ETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
b2	-	0.40	_	0.016
e1	1.5	1.55		061
l1	_	0.65	_	0.026

Dimension in mm / inches

## ●Dimensions (Unit : mm)

SMT6



Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	1.00	1.30	0.039	0.051	
A1	0.00	0.10	0.000	0.004	
A3	0.3	25	0.0	10	
b	0.25	0.40	0.010	0.016	
С	0.09	0.25	0.004	0.010	
D	2.80	3.00	0.110	0.118	
E	1.50	1.80	0.059	0.071	
е	0.95		0.95 0.037		37
HE	2.60	3.00	0.102	0.118	
L1	0.30	0.60	0.012	0.024	
Lp	0.40	0.70	0.016	0.028	
Q	0.20	0.30	0.008	0.012	
Х	_	0.20	_	0.008	
У	_	0.10	_	0.004	

MILIMETERS MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX
b2		0.60	-	0.024
e1	2.	0.083		083
l1	_	0.90	_	0.035

Dimension in mm / inches

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